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# MPS4250

## Transistor

### PNP Silicon

#### Features

- Pb-Free Packages are Available\*

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	–40	Vdc
Collector–Emitter Voltage	$V_{CES}$	–40	Vdc
Collector–Base Voltage	$V_{CBO}$	–40	Vdc
Emitter–Base Voltage	$V_{EBO}$	–5.0	Vdc
Collector Current – Continuous	$I_C$	–	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	W mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	–55 to +150	$^\circ\text{C}$

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

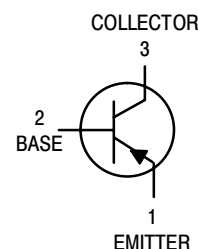
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

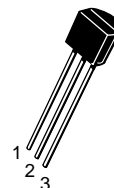


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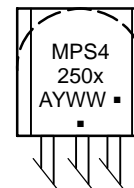
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#### MARKING DIAGRAM



TO-92  
CASE 29-11  
STYLE 1



MPS4250x = Device Code  
x = A\*  
\*MPS4250ARLRM  
\*MPS4250ARLRMG

A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping†
MPS4250	TO-92	5000/Tape & Reel
MPS4250G	TO-92 (Pb-Free)	5000/Tape & Reel
MPS4250ARLRM	TO-92	2000/Tape & Ammo
MPS4250ARLRMG	TO-92 (Pb-Free)	2000/Tape & Ammo

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MPS4250

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

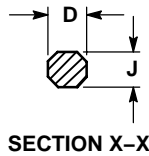
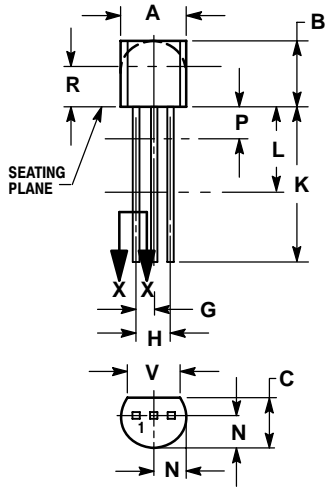
Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage ( $I_C = -5.0\text{ mA}$ )	$V_{(BR)CES}$	-40	-	Vdc
Collector–Emitter Sustaining Voltage (Note 1) ( $I_C = -5.0$ )	$V_{(BR)CEO(sus)}$	-40	-	Vdc
Collector–Base Breakdown Voltage ( $I_C = -10\ \mu\text{A}$ )	$V_{(BR)CBO}$	-40	-	Vdc
Emitter–Base Breakdown Voltage ( $I_E = -10\ \mu\text{A}$ )	$V_{(BR)EBO}$	-5.0	-	Vdc
Collector Cutoff Current ( $V_{CB} = -50\text{ V}$ ) ( $V_{CB} = -40\text{ V}$ , $T_A = 65^\circ\text{C}$ )	$I_{CBO}$	-	-10 -3.0	nA $\mu\text{A}$
Emitter Cutoff Current ( $V_{EB} = -3.0\text{ V}$ )	$I_{EBO}$	-	-20	nA
<b>ON CHARACTERISTICS</b>				
DC Current Gain ( $I_C = -1.0\text{ mA}$ , $V_{CE} = -5.0\text{ V}$ ) ( $I_C = -10\text{ mA}$ , $V_{CE} = -5.0\text{ V}$ )	$h_{FE}$	250 250	- -	-
Collector–Emitter Saturation Voltage (Note 1) ( $I_C = -10\text{ mA}$ , $I_B = -0.5\text{ mA}$ )	$V_{CE(sat)}$	-	-0.25	Vdc
Base–Emitter Saturation Voltage (Note 1) ( $I_C = -10\text{ mA}$ , $I_B = -0.5\text{ mA}$ )	$V_{BE(sat)}$	-	-0.9	Vdc
<b>SMALL–SIGNAL CHARACTERISTICS</b>				
Output Capacitance ( $V_{CB} = -5.0\text{ V}$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	-	6.0	pF
Input Capacitance ( $V_{EB} = -0.5\text{ V}$ , $f = 1.0\text{ MHz}$ )	$C_{ibo}$	-	16	pF
Small–Signal Current Gain ( $I_C = -1.0\text{ mA}$ , $V_{CE} = -5.0\text{ V}$ , $f = 1.0\text{ kHz}$ ) ( $I_C = -0.5\text{ mA}$ , $V_{CE} = -5.0\text{ V}$ , $f = 20\text{ MHz}$ )	$h_{fe}$	250 2.0	800 -	-
Noise Figure ( $I_C = -20\ \mu\text{A}$ , $V_{CE} = -5.0\text{ V}$ , $R_S = 10\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ , $P_{BW} = 150\text{ Hz}$ ) ( $I_C = -250\ \mu\text{A}$ , $V_{CE} = -5.0\text{ V}$ , $R_S = 1.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ , $P_{BW} = 150\text{ Hz}$ )	NF	- -	2.0 2.0	dB

1. Pulse Test: Pulse Width = 300  $\mu\text{s}$ ; Duty Cycle = 2.0%.

# MPS4250

## PACKAGE DIMENSIONS

TO-92 (TO-226)  
CASE 29-11  
ISSUE AL



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

### STYLE 1:

1. PIN 1. EMITTER
2. BASE
3. COLLECTOR

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